TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT5J301

HIGH POWER SWITCHING APPLICATIONS MOTOR CONTROL APPLICATIONS

• Third-generation IGBT

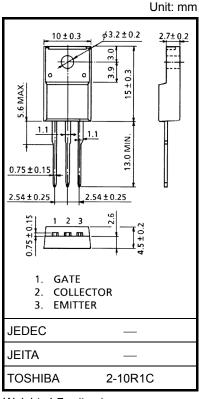
• Enhancement mode type

 $\begin{array}{ll} \bullet & \mbox{High speed} & : t_f = 0.30 \mu s \ (\mbox{Max.}) \ (\mbox{I}_C = 5 \mbox{A}) \\ \bullet & \mbox{Low saturation voltage} & : \mbox{VCE} \ (\mbox{sat)} = 2.7 \mbox{V} \ (\mbox{Max.}) \ (\mbox{I}_C = 5 \mbox{A}) \end{array}$

• FRD included between emitter and collector

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	600	V	
Gate-Emitter Voltage		V _{GES}	±20	V	
Collector Current	DC	Ic	5	Α	
	1ms	ICP	10	Α	
Emitter-Collector Forward Current	DC	lF	5	Α	
	1ms	I _{FM}	10	Α	
Collector Power Dissipation (Tc = 25°C)		PC	28	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-55~150	°C	

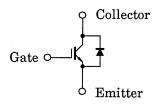


Weight: 1.7 g (typ.)

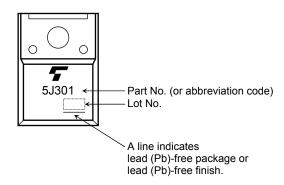
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

EQUIVALENT CIRCUIT



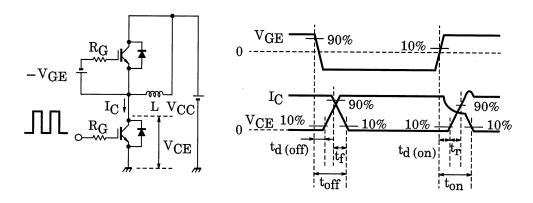
MARKING



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

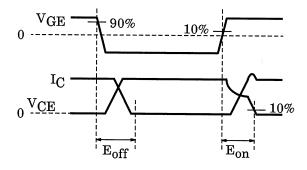
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I _{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	_	_	±500	nA
Collector Cut-Off Current		I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	_	1.0	mA
Gate-Emitter Cut-Off Voltage		V _{GE} (OFF)	I _C = 0.5mA, V _{CE} = 5V	5.0	_	8.0	V
Collector-Emitter S	Saturation Voltage	V _{CE} (sat)	I _C = 5A, V _{GE} = 15V	_	2.1	2.7	V
Input Capacitance		C _{ies}	V _{CE} = 20V, V _{GE} = 0, f = 1MHz	_	650	_	pF
Switching Time	Rise Time	t _r	Inductive Load V_{CC} = 300V, I_{C} = 5A V_{GG} = ±15V, R_{G} = 180 Ω (Note 1)	_	0.10	_	μs
	Turn-On Time	t _{on}		_	0.40	_	
	Fall Time	t _f		_	0.15	0.30	
	Turn-Off Time	t _{off}		_	0.30	_	
Peak Forward Voltage		V _F	I _F = 5A, V _{GE} = 0	_	_	1.8	V
Reverse Recovery Time		t _{rr}	I _F = 5A, di / dt = -100A / μs	_	_	200	ns
Thermal Resistance (IGBT)		R _{th (j-c)}	_	_	_	4.5	°C / W
Thermal Resistance (Diode)		R _{th (j-c)}	_	_	_	4.9	°C / W

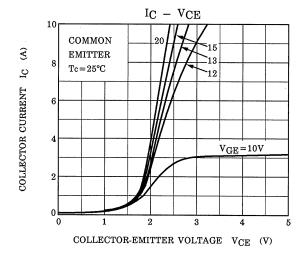
Note 1: Switching time measurement circuit and input / output waveforms

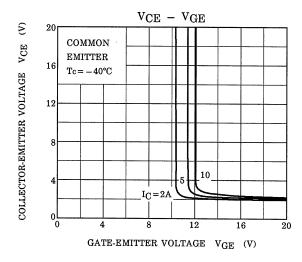


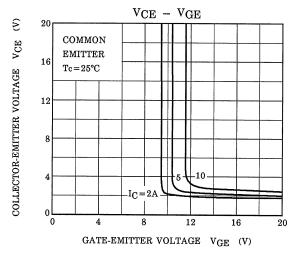
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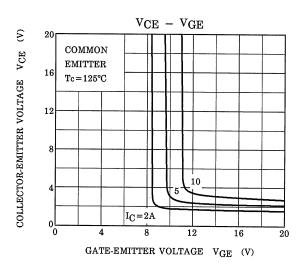
Switching loss measurement waveforms

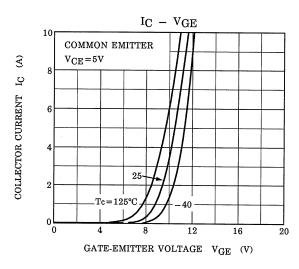


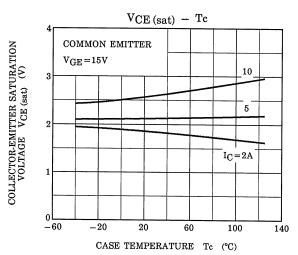




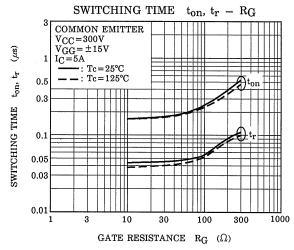


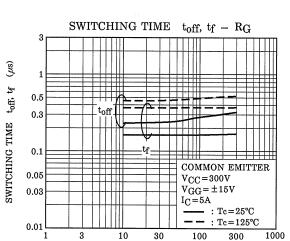




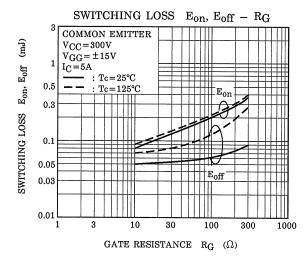


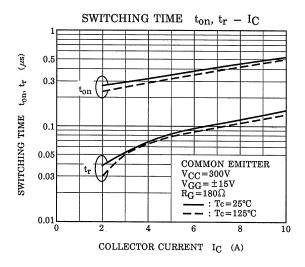
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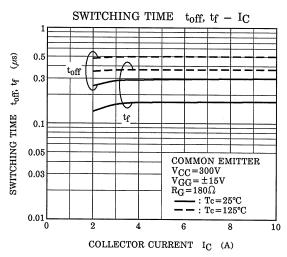


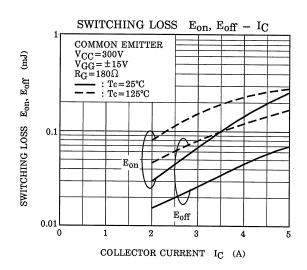


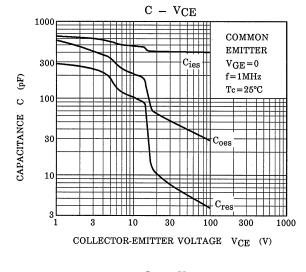
GATE RESISTANCE R_G (Ω)

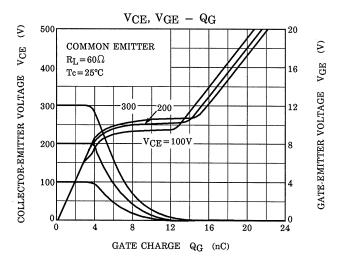


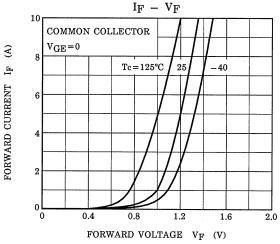


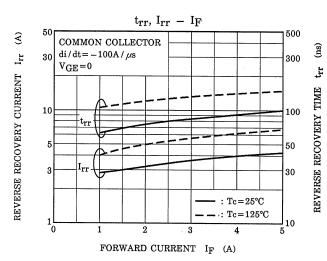


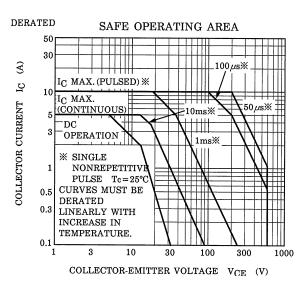


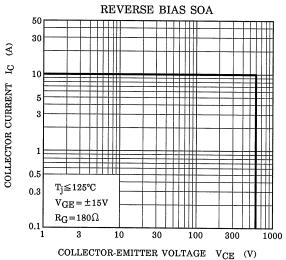




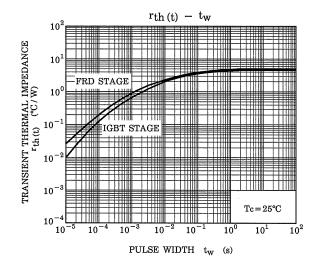








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